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# ***International Conference on Extreme Ultraviolet Lithography 2024***

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**30 September–3 October 2024**  
**Monterey, California, United States**

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SPIE

**Volume 13215**

Proceedings of SPIE 0277-786X, V. 13215

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

International Conference on Extreme Ultraviolet Lithography 2024, edited by Kurt G. Ronse, Patrick P. Naulleau,  
Paolo A. Gargini, Toshiro Itani, Joern-Holger Franke, Proc. of SPIE Vol. 13215, 1321501  
© 2024 SPIE · 0277-786X · doi: 10.1117/12.3056946

Proc. of SPIE Vol. 13215 1321501-1

The papers in this volume were part of the technical conference cited on the cover and title page. Papers were selected and subject to review by the editors and conference program committee. Some conference presentations may not be available for publication. Additional papers and presentation recordings may be available online in the SPIE Digital Library at [SPIDigitalLibrary.org](http://SPIDigitalLibrary.org).

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Please use the following format to cite material from these proceedings:

Author(s), "Title of Paper," in *International Conference on Extreme Ultraviolet Lithography 2024*, edited by Kurt G. Ronse, Patrick P. Naulleau, Paolo A. Gargini, Toshiro Itani, Joern-Holger Franke, Proc. of SPIE 13215, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X  
ISSN: 1996-756X (electronic)

ISBN: 9781510681552  
ISBN: 9781510681569 (electronic)

Published by

**SPIE**

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time)

[SPIE.org](http://SPIE.org)

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